

VENDREDI 24 Février  
14h30 - Amphithéâtre

## Magneto-ionics in CoFeB systems

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### Jury members

**Liza Herrera-Diez** : Thesis Director

**Rapporteur 1** : Karin Leistner, Professeure à la Technische Universität Chemnitz, Allemagne. (Externe à l'UPSaclay, pas de publications communes avec le candidat)

**Rapporteur 2** : Reinoud Lavrijsen, Professeur à la Eindhoven University of Technology, Les Pays-Bas.

**Examineur 1 et Présidente du jury** : Julie Grollier, Directrice de recherche CNRS à l'UMR CNRS-Thales, Palaiseau, France. (UPSaclay)

**Examineur 2** : Eva Pellicer, Professeure à la Universidad Autonoma de Barcelona, Espagne.

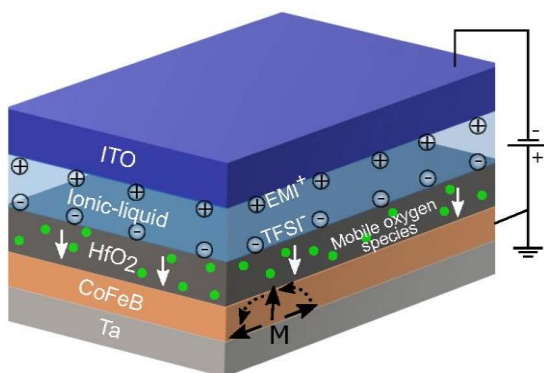
**Examineur 3** : Shimpei Ono, Chercheur au CRIEPI, Japon, et lauréat de la chaire d'Alembert de l'UPSaclay pour 'chercheur confirmé'.

**Examineur 4** : Mohamed Belmeguenai, Maître de conférence HDR à l'Université Sorbonne Paris Nord

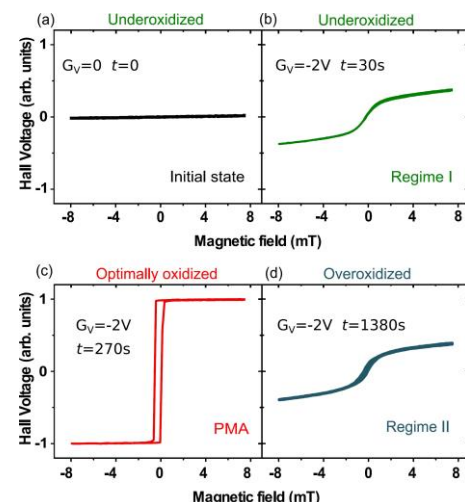
### Abstract

Electric field control of magnetic properties in ferromagnetic thin films is a sought-after feature for spintronics devices, as it offers great potential for high energy efficiency in memory applications.

Much like the power efficiency, two other sought-after features to incorporate are nonvolatility and reversibility. In addition to the effects arising from electric field-induced charge accumulation at the ferromagnet/dielectric interface, electric field-induced migration of ions in dielectric layers adjacent to a magnetic layer shows a more extended effect, resolving electrostatic screening and volatility of charges. Such a technique is known as magneto-ionics. Magneto-ionic control of magnetic properties using oxygen ions has been of great importance in developing energy efficient spintronics devices; however, the magneto-ionic performance such as speed, reversibility and stability is largely influenced by the stack materials. In this thesis, CoFeB-based systems are explored for various heavy metal buffer layers optimizing magneto-ionic performance addressing the importance of factors such as the level of oxidation, post-growth annealing and the stability.



Graphic representation of the Ta/CoFeB/HfO<sub>2</sub> magnetoionic stack covered with the ionic liquid [EMI]<sup>+</sup>[TFSI]<sup>-</sup> gate. The gate voltage induces the motion of oxygen species in HfO<sub>2</sub>



A progressive oxidation is induced upon exposure to a gate voltage  $G_V = -2$  V. Different exposure times  $t$  drive the system from IPA (a, initial state) through regime I (b) into PMA (c) and back to IPA through regime II (d).

